

NTE87 (NPN) & NTE88 (PNP) Silicon Complementary Transistors High Power Audio, Disk Head Positioner for Linear Applications

Description:

The NTE87 (NPN) and NTE88 (PNP) are complementary silicon power transistors in a TO3 type package designed for high power audio, disk head positioners, and other linear applications. These devices can also be used in power switching circuits such as relay or solenoid drivers, DC-to-DC converters or inverters.

Features:

- High Safe Operating Area: 1.2A @ 100V
- Completely Characterized for Linear Operation
- High DC Current Gain: $h_{FE} = 20$ Min @ $I_C = 2A$
- Low Saturation Voltage: 2V
- For Low Distortion Complementary Designs

Absolute Maximum Ratings:

Collector-Emitter Voltage, $V_{CEO(sus)}$	250V
Collector-Emitter Voltage, V_{CEX}	250V
Emitter-Base Voltage, V_{EB}	5V
Collector Current, I_C	
Continuous	10A
Peak (Note 2)	15A
Base Current, I_B	
Continuous	2A
Peak (Note 2)	5A
Emitter Current, I_E	
Continuous	12A
Peak (Note 2)	20A
Total Power Dissipation ($T_C = +25^\circ C$), P_D	200W
Derate Above $25^\circ C$	1.14W/ $^\circ C$
Operating Junction Temperature Range, T_J	-65° to $+200^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ C$
Thermal Resistance, Junction-to-Case, R_{thJC}	0.875 $^\circ C/W$
Lead Temperature (During Soldering), T_L	$+265^\circ C$

Note 1. Matched complementary pairs are available upon request (NTE88MCP). Matched complementary pairs have their gain specification (h_{FE}) matched to within 10% of each other.

Note 2. Pulse Test: Pulse Width = 5ms, Duty Cycle $\leq 10\%$.

Electrical Characteristics: ($T_C = +25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Breakdown Voltage	V _{CEO(sus)}	I _C = 100mA, Note 3	250	–	–	V
Collector Cutoff Current	I _{CEO}	V _{CE} = 250V	–	–	1	mA
	I _{CEX}	V _{CE} = 250V, V _{BE(off)} = 1.5V	–	–	500	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 5V	–	–	500	μA
Second Breakdown						
Second Breakdown Collector Current with Base Forward Bias	I _{S/b}	V _{CE} = 40V, t = 0.5s (non–repetitive)	5	–	–	A
		V _{CE} = 100V, t = 0.5s (non–repetitive)	1.4	–	–	A
ON Characteristics (Note 3)						
DC Current Gain	h _{FE}	V _{CE} = 2V, I _C = 2A	20	–	100	
		V _{CE} = 2V, I _C = 4A	5	–	–	
Collector–Emitter Saturation Voltage	V _{CE(sat)}	I _C = 2A, I _B = 200mA	–	–	0.8	V
		I _C = 4A, I _B = 400mA	–	–	2.5	V
Base–Emitter On Voltage	V _{BE(on)}	V _{CE} = 2V, I _C = 4A	–	–	2	V
Dynamic Characteristics						
Current Gain–Bandwidth Product	f _T	V _{CE} = 10V, I _C = 1A, f _{test} = 1MHz	4	–	–	MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f _{test} = 1MHz	–	–	500	pF

Note 3. Pulse Test: Pulse Width = $300\mu\text{s}$, Duty Cycle $\leq 2\%$.

